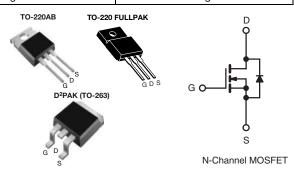




### **Power MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V) at T <sub>J</sub> max.	560 \	/		
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V	0.555		
Q <sub>g</sub> (Max.) (nC)	48			
Q <sub>gs</sub> (nC)	12			
Q <sub>gd</sub> (nC)	15			
Configuration	Single	е		



#### **FEATURES**

- ullet Low Figure-of-Merit  $R_{on} \ x \ Q_g$
- 100 % Avalanche Tested
- Gate Charge Improved
- T<sub>rr</sub>/Q<sub>rr</sub> Improved
- Compliant to RoHS Directive 2002/95/EC





ORDERING INFORMATION				
Package	TO-220AB	D <sup>2</sup> PAK (TO-263)	TO-220 FULLPAK	
Lead (Pb)-free	SiHP12N50C-E3	SiHB12N50C-E3	SiHF12N50C-E3	

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)							
				LIM			
PARAMETER			SYMBOL	TO220-AB D <sup>2</sup> PAK (TO-263)	TO-220 FULLPAK	UNIT	
Drain-Source Voltage			V <sub>DS</sub>	500		V	
Gate-Source Voltage			V <sub>GS</sub>	± 30		\ \	
Ocation	\/ at 10\/	T <sub>C</sub> = 25 °C		12			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 100 °C	I <sub>D</sub>	7.5	5	Α	
Pulsed Drain Current <sup>c</sup>			I <sub>DM</sub>	28			
Linear Derating Factor				1.67	0.28	W/°C	
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	180		mJ	
Maximum Power Dissipation			$P_{D}$	208	36	W	
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150		°C	
Soldering Recommendations (Peak Temperature)d	for	10 s		300		- 'C	

#### Notes

- a. Limited by maximum junction temperature.
- b.  $V_{DD}$  = 50 V, starting  $T_J$  = 25 °C, L = 2.5 mH,  $R_q$  = 25  $\Omega$ ,  $I_{AS}$  = 12 A.
- c. Repetitive rating; pulse width limited by maximum junction temperature.
- d. 1.6 mm from case.

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply

# SiHP12N50C, SiHB12N50C, SiHF12N50C

# Vishay Siliconix



THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TO220-AB D <sup>2</sup> PAK (TO-263)	TO-220 FULLPAK	UNIT	
Maximum Junction-to-Ambient	R <sub>thJA</sub>	62	65		
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	0.6	3.5	°C/W	
Junction-to-Ambient (PCB mount) <sup>a</sup>	R <sub>thJA</sub>	40	-		

#### Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

PARAMETER	SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$	500	-	-	V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference t	-	0.6	-	V/°C	
Gate-Source Threshold Voltage (N)	V <sub>GS(th)</sub>	$V_{DS} = V$	$V_{DS} = V_{GS}, I_D = 250 \mu A$		-	5.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>G</sub>	S = ± 30 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	l	$V_{DS} = 50$	00 V, V <sub>GS</sub> = 0 V	-	-	50	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 400 \text{ V}, \text{ V}$	$t_{\rm GS} = 0 \text{ V}, T_{\rm J} = 125  ^{\circ}\text{C}$	-	-	250	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 4 A	-	0.46	0.555	Ω
Forward Transconductance	9 <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 3 A		-	3	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	$V_{GS} = 0 \text{ V},$ $V_{DS} = 25 \text{ V},$ f = 1.0  MHz		-	1375	-	
Output Capacitance	C <sub>oss</sub>			-	165	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	17	-	
Total Gate Charge	$Q_g$			-	32	48	
Gate-Source Charge	$Q_{gs}$	V <sub>GS</sub> = 10 V	$I_D = 10 \text{ A}, V_{DS} = 400 \text{ V}$	-	12	-	nC
Gate-Drain Charge	$Q_{gd}$	]		-	15	-	
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DD}$ = 250 V, $I_{D}$ = 10 A $R_{g}$ = 4.3 $\Omega$ , $V_{GS}$ = 10 V		-	18	-	- ns
Rise Time	t <sub>r</sub>			-	35	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	23	-	
Fall Time	t <sub>f</sub>			-	6	-	
Gate Input Resistance	$R_g$	f = 1 MHz, open drain		-	1.1	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	12	А
Pulsed Diode Forward Current	I <sub>SM</sub>			-	-	28	^
Body Diode Voltage	$V_{SD}$	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 10 A, V <sub>GS</sub> = 0 V		-	-	1.8	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> , dI/dt = 100 A/μs, V <sub>R</sub> = 20 V		-	580	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			_	4.3	-	μC
Body Diode Reverse Recovery Current	I <sub>RRM</sub>			-	13	-	Α

#### Note

• The information shown here is a preliminary product proposal, not a commercial product data sheet. Vishay Siliconix is not committed to produce this or any similar product. This information should not be used for design purposes, nor construed as an offer to furnish or sell such products.

### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

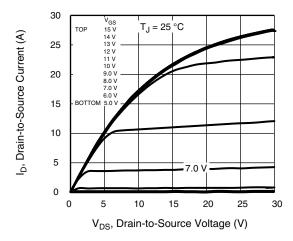


Fig. 1 - Typical Output Characteristics (TO-220)

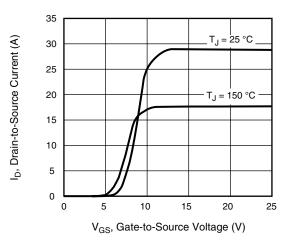


Fig. 3 - Typical Transfer Characteristics

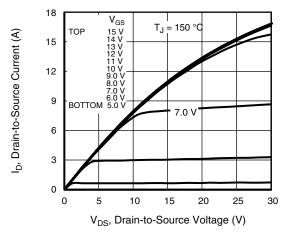


Fig. 2 - Typical Output Characteristics (TO-220)

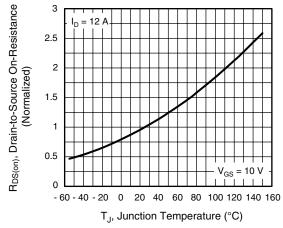


Fig. 4 - Normalized On-Resistance vs. Temperature



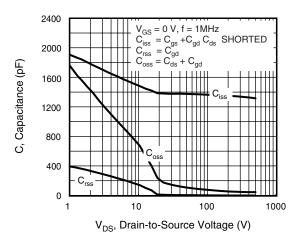


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

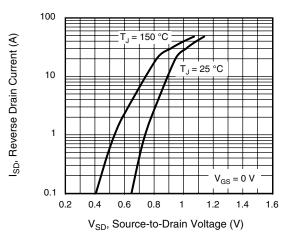


Fig. 7 - Typical Source-Drain Diode Forward Voltage

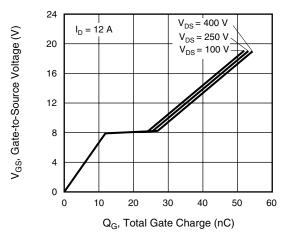


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

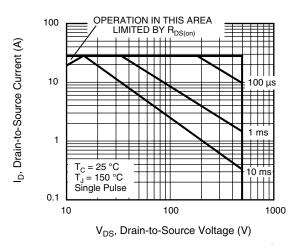


Fig. 8 - Maximum Safe Operating Area (TO-220AB, D2PAK)

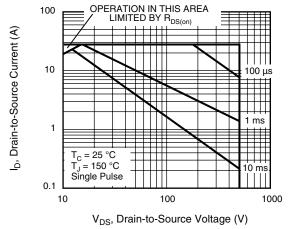


Fig. 9 - Maximum Safe Operating Area (TO-220 FULLPAK)

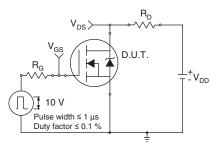


Fig. 10a - Switching Time Test Circuit

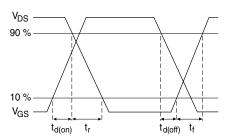


Fig. 10b - Switching Time Waveforms

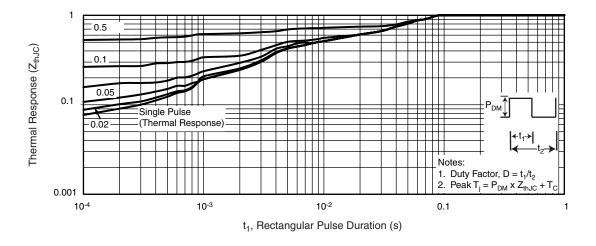


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220AB, D2PAK)

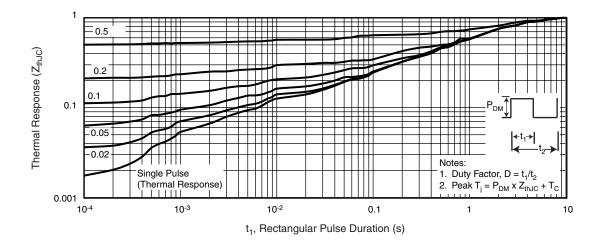


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220 FULLPAK)



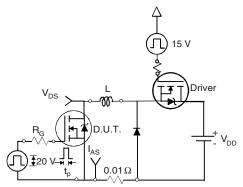


Fig. 13a - Unclamped Inductive Test Circuit

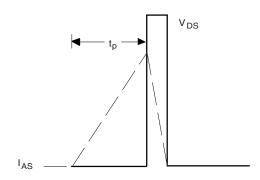


Fig. 13b - Unclamped Inductive Waveforms

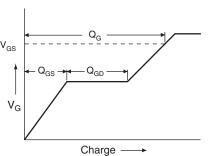


Fig. 14a - Basic Gate Charge Waveform

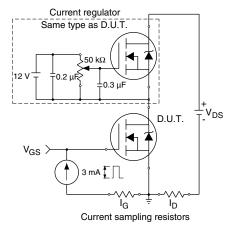
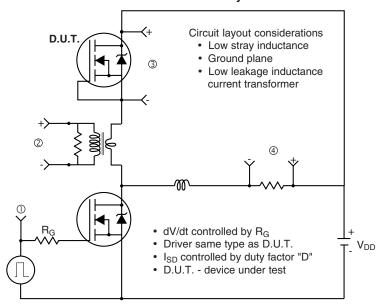
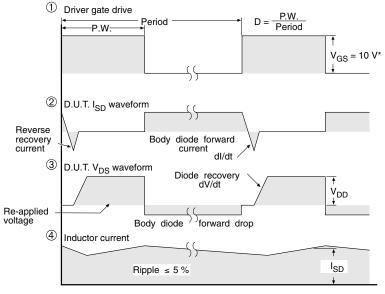


Fig. 14b - Gate Charge Test Circuit



#### Peak Diode Recovery dV/dt Test Circuit





<sup>\*</sup> V<sub>GS</sub> = 5 V for logic level devices

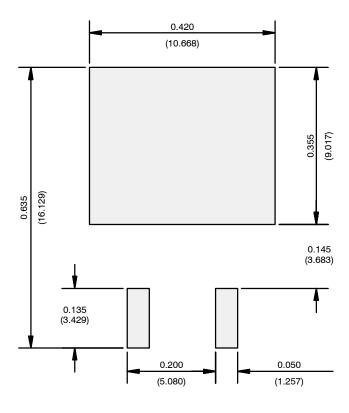
Fig. 15 - For N-Channel

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### RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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